TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

S5295B, S5295G, S5295J

HIGH SPEED RECTIFIER APPLICATIONS. (FAST RECOVERY)

Unit in mm

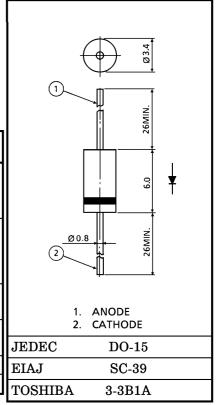
 $: I_{F(AV)} = 0.5 A (Ta = 50^{\circ}C)$ Average Forward Current

: $V_{RRM} = 100 \sim 600 \text{ V}$ Repetitive Peak Reverse Voltage

Reverse Recovery Time : 1.5 μ s

MAXIMUM RATING

CHARACTERISTIC		SYMBOL	RATING	UNIT
D. CC. D. I. D.	S5295B	$v_{ m RRM}$	100	V
Repetitive Peak Reverse Voltage	S5295G		400	
	S5295J		600	
Reverse Voltage (DC)	S5295B	v_{R}	75	V
	S5295G		300	
	S5295J		500	
Average Forward Current (Ta = 50°C)		I _{F (AV)}	0.5	A
Peak One Cycle Surge Forward Current (Non Repetitive)		I_{FSM}	30 (50 Hz)	A
Junction Temparature		$T_{\rm j}$	-40~125	°C
Storage Temparature Range		$\mathrm{T_{stg}}$	-40~125	$^{\circ}\mathrm{C}$

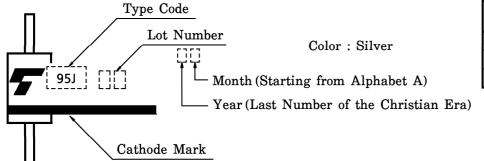


Weight: 0.42 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Peak Forward Voltage	$v_{ m FM}$	$I_{\text{FM}} = 1.0 \text{ A}$		1.5	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{ m RRM} = { m Rated}$		10	μ A
Reverse Recovery Time	t_{rr}	$I_{\mathrm{F}}=20\mathrm{mA},~I_{\mathrm{R}}=1\mathrm{mA}$		1.5	μs
Forward Recovery Voltage	$ m V_{fr}$	$I_{ m F}=100~{ m mA},~t_{ m r}=100~{ m ns},~t_{ m W}=5~\mu{ m s}$		10	V

MARKING



CODE	TYPE
95B	S5295B
95G	S5295G
95J	S5295J

961001EAA2

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